

Abstract of the Disclosure

A semiconductor light emitting device is formed by adhering a semiconductor layered portion having a light emitting layer forming portion to a conductive substrate via a metal layer. The metal layer has at least a first metal layer for ohmic contact with the semiconductor layered portion, a second metal layer made of Ag, and a third metal layer made of a metal which allows adhesion to the conductive substrate at a low temperature. As a result, the rate of reflection of light from the metal layer increases due to the presence of Ag in the metal layer. Further, the metal in the metal layer is prohibited from diffusing into the semiconductor layer, so that the semiconductor layer does not absorb light. And therefore the brightness of the semiconductor light emitting device can further be increased.